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November 2008

# FDZ391P P-Channel 1.5 V PowerTrench<sup>®</sup> Thin WL-CSP MOSFET -20 V, -3 A, 85 mΩ

## Features

- Max  $r_{DS(on)}$  = 85 m $\Omega$  at  $V_{GS}$  = -4.5 V,  $I_D$  = -1 A
- Max  $r_{DS(on)}$  = 123 m $\Omega$  at V<sub>GS</sub> = -2.5 V, I<sub>D</sub> = -1 A
- Max  $r_{DS(on)}$  = 200 m $\Omega$  at V<sub>GS</sub> = -1.5 V, I<sub>D</sub> = -1 A
- Occupies only 1.5 mm<sup>2</sup> of PCB area
- Ultra-thin package: less than 0.4 mm height when mounted to PCB
- RoHS Compliant

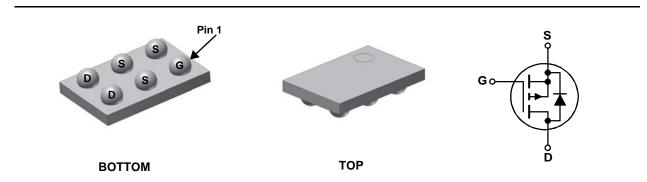


# **General Description**

Designed on Fairchild's advanced 1.5 V PowerTrench process with state of the art "low pitch" **Thin** WLCSP packaging process, the FDZ391P minimizes both PCB space and  $r_{DS(on)}$ . This advanced WLCSP MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, ultra-low profile packaging, low gate charge, and low  $r_{DS(on)}$ .

# Applications

- Battery management
- Load switch
- Battery protection



## MOSFET Maximum Ratings T<sub>A</sub> = 25 °C unless otherwise noted

Symbol	Par		Ratings	Units		
V <sub>DS</sub>	Drain to Source Voltage		-20	V		
V <sub>GS</sub>	Gate to Source Voltage			±8	V	
	Drain Current -Continuous	T <sub>A</sub> = 25 °C	(Note 1a)	-3	۸	
D	-Pulsed			-15	Α	
D	Power Dissipation	T <sub>A</sub> = 25 °C	(Note 1a)	1.9	14/	
P <sub>D</sub>	Power Dissipation	T <sub>A</sub> = 25 °C	(Note 1b)	0.9	W	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temp	perature Range		-55 to +150	°C	

### **Thermal Characteristics**

$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	65	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	133	C/VV

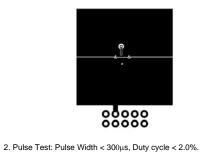
### **Package Marking and Ordering Information**

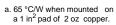
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
6	FDZ391P	WL-CSP Thin	7 "	8 mm	5000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Chara	cteristics						
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	I <sub>D</sub> = -250 μA, V <sub>GS</sub> = 0 V	-20			V	
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \ \mu\text{A}$ , referenced to 25 °C		-12		mV/°C	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -16 V, V_{GS} = 0 V$			-1	μA	
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA	
On Chara	cteristics						
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \ \mu A$	-0.4	-0.6	-1.5	V	
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250 \ \mu$ A, referenced to 25 °C		2		mV/°C	
r <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -1 A		74	85	- mΩ	
		$V_{GS} = -2.5 \text{ V}, I_D = -1 \text{ A}$		90	123		
		$V_{GS} = -1.5 \text{ V}, \text{ I}_{D} = -1 \text{ A}$		140	200		
		$V_{GS}$ = -4.5 V, $I_{D}$ = -1 A T <sub>J</sub> = 125 °C		100	123		
I <sub>D(on)</sub>	On to State Drain Current	$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-10			Α	
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = -5 V, I_{D} = -1 A$		7		S	
Dynamic	Characteristics						
C <sub>iss</sub>	Input Capacitance	N 40.4 M 0.4		800	1065	pF	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		155	205	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			90	135	pF	
R <sub>g</sub>	Gate Resistance	f = 1 MHz		9		Ω	
Switching	g Characteristics						
t <sub>d(on)</sub>	Turn-On Delay Time			11	20	ns	
t <sub>r</sub>	Rise Time	$V_{DD} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ A}$		10	20	ns	
t <sub>d(off)</sub>	Turn-Off Delay Time	$-$ V <sub>GS</sub> = -4.5 V, R <sub>GEN</sub> = 6 $\Omega$		50	80	ns	
t <sub>f</sub>	Fall Time			30	48	ns	
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> = -4.5 V		9	13	nC	
Q <sub>gs</sub>	Gate to Source Gate Charge	$V_{DD} = -10 V$		1		nC	
Q <sub>gd</sub>	Gate to Drain "Miller" Charge	I <sub>D</sub> = -1 A		2		nC	
Drain-Sou	urce Diode Characteristics						
I <sub>S</sub>	Maximum continuous Drain-Source Dio	de Forward Current			-1.1	Α	
	Source to Drain Diade, Forward Voltage			0.7	10	V	

I <sub>S</sub>	Maximum continuous Drain-Source Diode Forward Current			-1.1	А
$V_{SD}$	Source to Drain Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -1.1 A (Note 2)	-0.7	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	- I <sub>F</sub> = -1 A, di/dt = 100 A/μs	21		ns
Q <sub>rr</sub>	Reverse Recovery Charge	$F = -1 A, avat = 100 A/\mu S$	5		nC

Notes: 1. R<sub>θJA</sub> is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design.

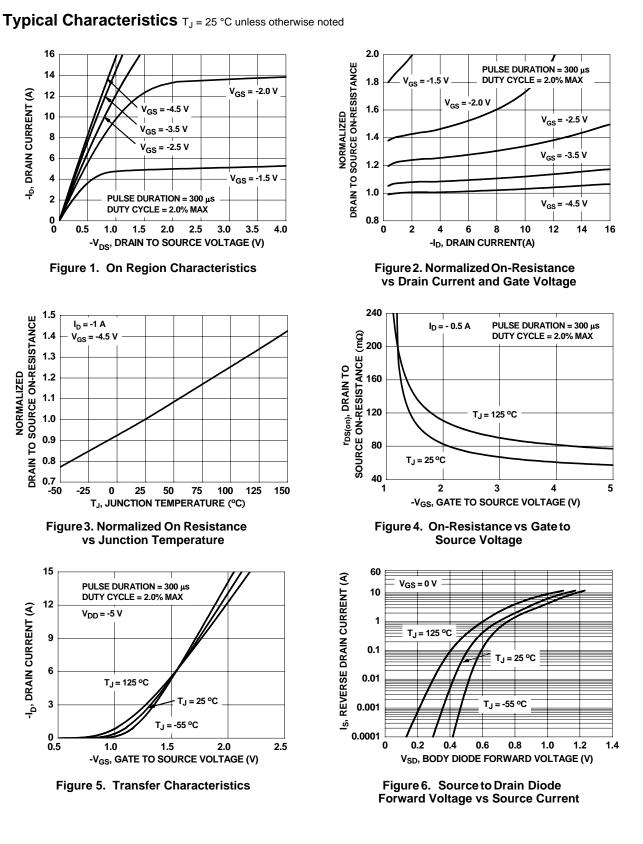




b. 133 °C/W when mounted on a minimum pad of 2 oz copper.



FDZ391P P-Channel 1.5V PowerTrench<sup>®</sup> WL-CSP MOSFET



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FDZ391P Rev.B1

-I<sub>D</sub>, DRAIN CURRENT (A)

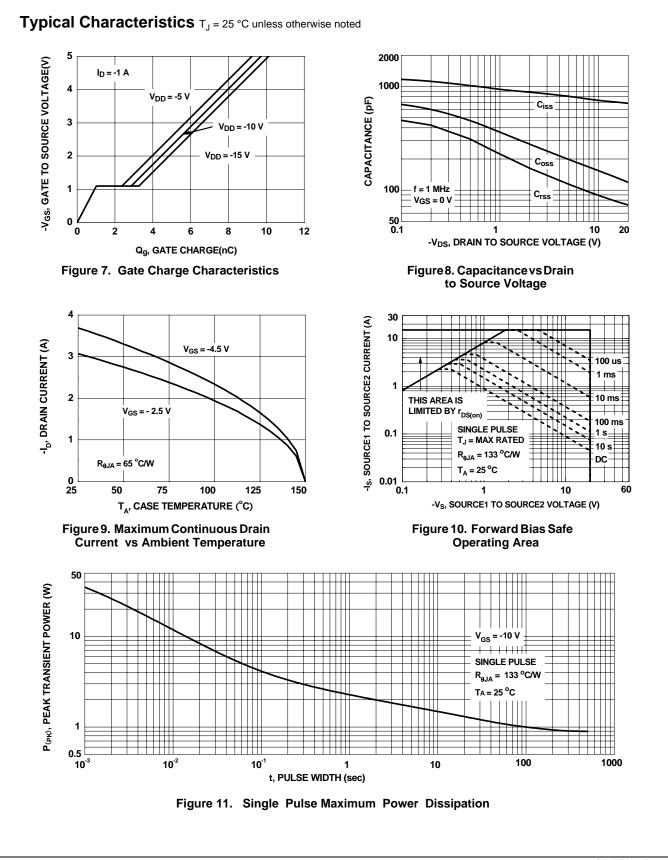
-I<sub>D</sub>, DRAIN CURRENT (A)

DRAIN TO SOURCE ON-RESISTANCE

NORMALIZED

3

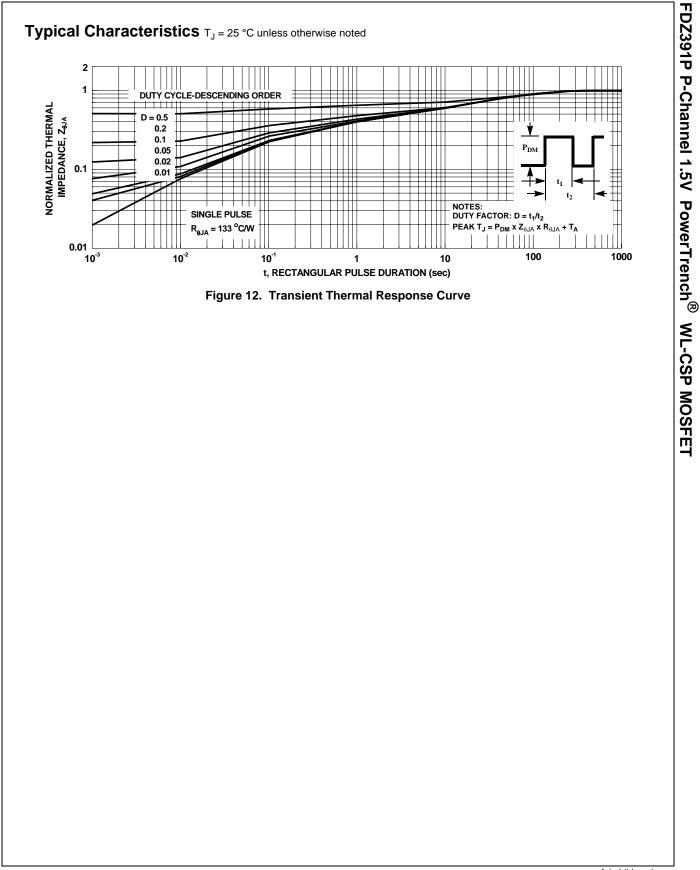
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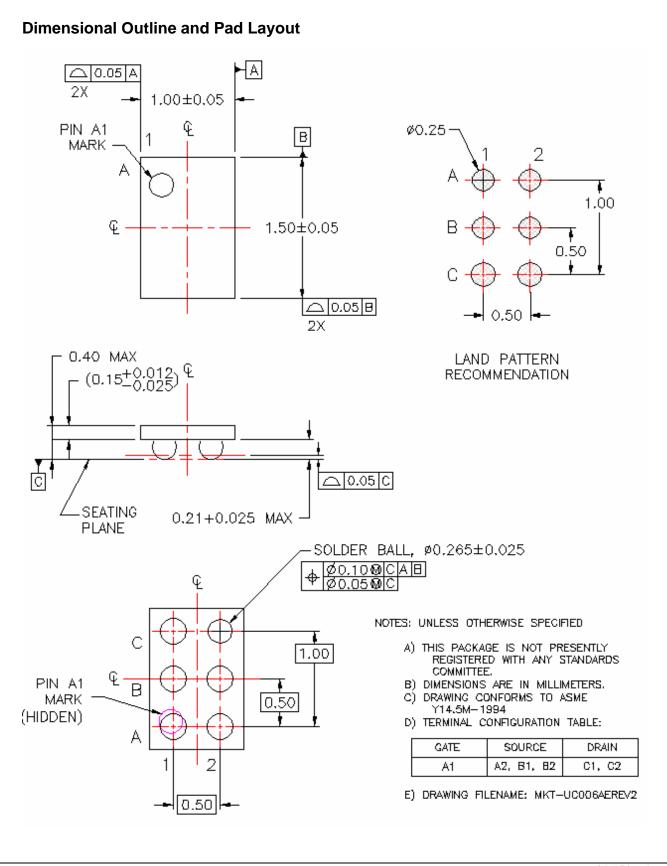


FDZ391P Rev.B1

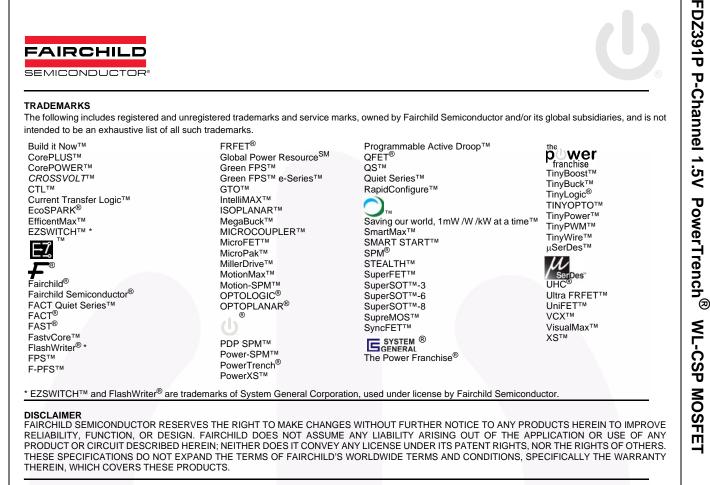
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